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Bus Buffer Gate with 3-state Output



ADE-205-324D (Z)

5th. Edition Feb. 2003

Description

The HD74LV1G126A has a bus buffer gate with 3–state output in a 5 pin package. Output is disabled when the associated output enable (OE) input is low. To ensure the high impedance state during power up or power down, OE should be connected to $V_{\rm cc}$ through a pull-down resistor; the minimum value of the resistor is determined by the current souring capability of the driver. Low voltage and high speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

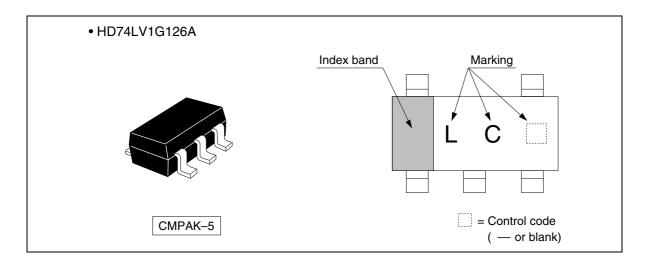
Features

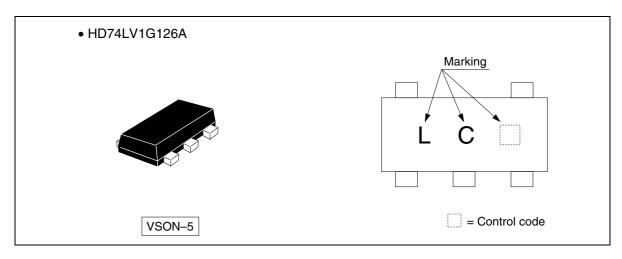
- The basic gate function is lined up as hitachi uni logic series.
- Supplied on emboss taping for high speed automatic mounting.
- Electrical characteristics equivalent to the HD74LV126A Supply voltage range: 1.65 to 5.5 V
 Operating temperature range: -40 to +85°C
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V) All outputs V_{O} (Max.) = 5.5 V (@ V_{CC} = 0 V, Output : Z)
- Output current $\pm 6 \text{ mA}$ (@V_{cc} = 3.0 V to 3.6 V), $\pm 12 \text{ mA}$ (@V_{cc} = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LV1G126ACME	CMPAK-5 pin	CMPAK-5V	CM	E (3,000 pcs/reel)
HD74LV1G126AVSE	VSON-5 pin	TNP-5DV	VS	E (3,000 pcs/reel)

Note: Please consult the sales office for the above package availability.

Outline and Article Indication



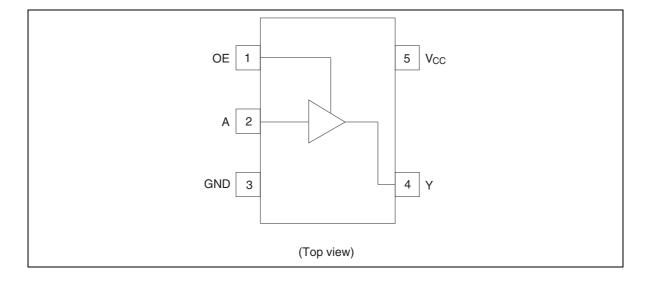


Function Table

Inputs		Output Y
OE	Α	
Н	Н	Н
Н	L	L
L	Х	Z

H : High level
L : Low level
X : Immaterial
Z : High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{cc}	-0.5 to 7.0	V	
Input voltage range *1	V _i	-0.5 to 7.0	V	
Output voltage range *1,2	V _o	-0.5 to $V_{cc} + 0.5$	V	Output : H or L
		-0.5 to 7.0		V _{cc} : OFF or Output : Z
Input clamp current	I _{IK}	-20	mA	V ₁ < 0
Output clamp current	I _{ok}	±50	mA	$V_{o} < 0 \text{ or } V_{o} > V_{cc}$
Continuous output current	I _o	±25	mA	$V_{o} = 0$ to V_{cc}
Continuous current through V_{cc} or GND	I _{CC} or I _{GND}	±50	mA	
Maximum power dissipation at Ta = 25°C (in still air) ³	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes:

The absolute maximum ratings are values which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{cc}	1.65	5.5	V	
Input voltage range	V _I	0	5.5	V	
Output voltage range	V _o	0	V _{cc}	V	
		0	5.5		Output : Z
Output current	I _{oL}	_	1	mA	V _{cc} = 1.65 to 1.95 V
		_	2		$V_{cc} = 2.3 \text{ to } 2.7 \text{ V}$
		_	6		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		_	12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
	I _{OH}	_	-1		V_{cc} = 1.65 to 1.95 V
			-2		$V_{cc} = 2.3 \text{ to } 2.7 \text{ V}$
			-6		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
			-12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Input transition rise or fall rate	Δt / Δν	0	300	ns / V	$V_{cc} = 1.65 \text{ to } 1.95 \text{ V}$
		0	200		$V_{cc} = 2.3 \text{ to } 2.7 \text{ V}$
		0	100		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		0	20		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Operating free-air temperature	T _a	-40	85	°C	

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Note: Unused or floating inputs must be held high or low.

Electrical Characteristic

• $Ta = -40 \text{ to } 85^{\circ}\text{C}$

Item	Symbol	V _{cc} (V) *	Min	Тур	Max	Unit	Test condition
Input voltage	V _{IH}	1.65 to 1.95	V _{cc} ×0.75	_	_	V	
		2.3 to 2.7	V _{cc} ×0.7	_	_	_	
		3.0 to 3.6	V _{cc} ×0.7	_	_	_	
		4.5 to 5.5	V _{cc} ×0.7	_	_	_	
	V _{IL}	1.65 to 1.95	_	_	V _{cc} ×0.25	_	
		2.3 to 2.7	_	_	V _{cc} ×0.3	_	
		3.0 to 3.6	_	_	V _{cc} ×0.3	_	
		4.5 to 5.5	_	_	V _{cc} ×0.3	_	
Hysteresis voltage	V _H	1.8	_	0.25	_	V	$V_{\scriptscriptstyle T}^{\scriptscriptstyle +} - V_{\scriptscriptstyle T}^{\scriptscriptstyle -}$
		2.5	_	0.30	_	_	
		3.3	_	0.35	_	_	
		5.0	_	0.45	_	_	
Output voltage	V _{OH}	Min to Max	V _{cc} -0.1	_	_	V	$I_{OH} = -50 \ \mu A$
		1.65	1.4	_	_	_	$I_{OH} = -1 \text{ mA}$
		2.3	2.0	_	_	_	$I_{OH} = -2 \text{ mA}$
		3.0	2.48	_	_	_	$I_{OH} = -6 \text{ mA}$
		4.5	3.8	_	_	_	$I_{OH} = -12 \text{ mA}$
	V _{OL}	Min to Max	_	_	0.1		$I_{OL} = 50 \mu A$
		1.65	_	_	0.3	_	I _{OL} = 1 mA
		2.3	_	_	0.4	_	I _{OL} = 2 mA
		3.0	_	_	0.44		I _{OL} = 6 mA
		4.5	_	_	0.55	_	I _{OL} = 12 mA
Input current	I _{IN}	0 to 5.5	_	_	±1	μΑ	V _{IN} = 5.5 V or GND
Off state output current	l _{oz}	Min to Max	_	_	±5	μА	$V_o = 5.5 \text{ V or GND}$
Quiescent supply current	I _{cc}	5.5	_	_	10	μА	$V_{IN} = V_{CC}$ or GND, $I_{O} = 0$
Output leakage current	l _{OFF}	0	_	_	5	μА	V_{IN} or $V_{O} = 0$ to 5.5 V
Input capacitance	C _{IN}	3.3	_	3.0	_	pF	$V_{IN} = V_{CC}$ or GND
						_	

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

• $V_{CC} = 1.8 \pm 0.15 \text{ V}$

Item	Symbol	Ta = 2	25°C		Ta = -	40 to 85°C	Unit	Test	FROM	то
		Min	Тур	Max	Min	Max	_	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	13.5	23.5	1.0	26.0	ns	C _∟ = 15 pF	Α	Υ
delay time	$t_{_{PHL}}$	_	19.0	33.0	1.0	36.0	_	C _∟ = 50 pF	_	
Enable time	t _{zH}	_	13.7	26.5	1.0	29.0	ns	C _L = 15 pF	OE	Υ
	$\mathbf{t}_{\scriptscriptstyle \mathrm{ZL}}$	_	20.5	36.0	1.0	38.0	_	C _L = 50 pF	_	
Disable time	t _{HZ}	_	8.3	20.0	1.0	22.5	ns	C _L = 15 pF	OE	Υ
	\mathbf{t}_{LZ}	_	13.0	29.5	1.0	32.0	_	C _L = 50 pF	_	

• $V_{CC} = 2.5 \pm 0.2 \text{ V}$

Item	Symbol	Ta =	25°C		Ta = -	40 to 85°C	Unit	Test	FROM	то
		Min	Тур	Max	Min	Max	_	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	7.1	13.0	1.0	15.5	ns	C _L = 15 pF	Α	Υ
delay time	$t_{_{PHL}}$	_	9.2	16.5	1.0	18.5	_	C _L = 50 pF	_	
Enable time	t _{zH}	_	7.4	13.0	1.0	15.5	ns	C _L = 15 pF	OE	Υ
	$\mathbf{t}_{_{\mathrm{ZL}}}$	_	9.5	16.5	1.0	18.5	=	C _L = 50 pF	_	
Disable time	t _{HZ}	_	5.7	14.7	1.0	17.0	ns	C _L = 15 pF	OE	Υ
	$\mathbf{t}_{\scriptscriptstyle{LZ}}$	_	8.1	18.2	1.0	20.5	_	C _L = 50 pF	=	

• $V_{cc} = 3.3 \pm 0.3 \text{ V}$

Item	Symbol	Ta = 2	25°C		Ta = -40 to 85° C		Unit	Test	FROM	TO
		Min	Тур	Max	Min	Max	-	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	5.0	8.0	1.0	9.5	ns	C _L = 15 pF	Α	Υ
delay time	$t_{_{PHL}}$	_	6.4	11.5	1.0	13.0	_	C _∟ = 50 pF	_	
Enable time	t _{zH}	_	5.1	8.0	1.0	9.5	ns	C _L = 15 pF	OE	Υ
	$\mathbf{t}_{\scriptscriptstyle{\mathrm{ZL}}}$	_	6.6	11.5	1.0	13.0	_	C _L = 50 pF	_	
Disable time	$t_{\scriptscriptstyle HZ}$	_	4.4	9.7	1.0	11.5	ns	C _L = 15 pF	OE	Υ
	t _{LZ}	_	6.1	13.2	1.0	15.0		C _L = 50 pF		

Switching Characteristics (cont)

• $V_{CC} = 5.0 \pm 0.5 \text{ V}$

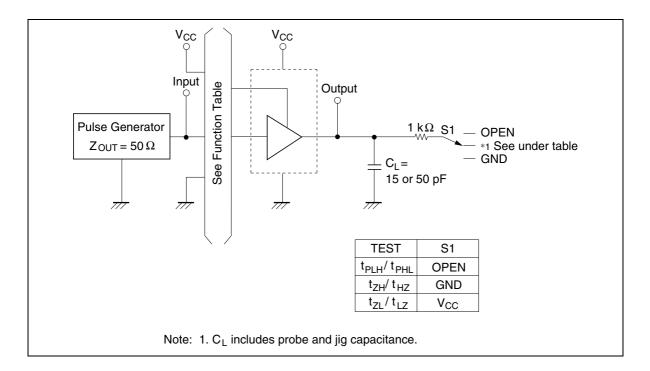
Item	Symbol	Ta = :	25°C		Ta = -40 to 85°C		Unit	Test	FROM	то
		Min	Тур	Max	Min	Max	-	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	3.5	5.5	1.0	6.5	ns	C _∟ = 15 pF	Α	Υ
delay time	$t_{_{PHL}}$	_	4.6	7.5	1.0	8.5	_	C _∟ = 50 pF	_	
Enable time	t _{zH}	_	3.6	5.1	1.0	6.0	ns	C _L = 15 pF	OE	Υ
	$\mathbf{t}_{\scriptscriptstyle ZL}$	_	4.6	7.1	1.0	8.0	_	C _∟ = 50 pF	_	
Disable time	t _{HZ}		3.3	6.8	1.0	8.0	ns	C _L = 15 pF	OE	Υ
	\mathbf{t}_{LZ}	_	4.3	8.8	1.0	10.0		C _L = 50 pF	_	

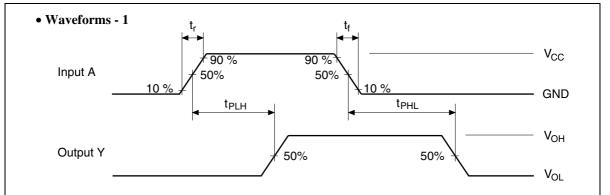
Operating Characteristics

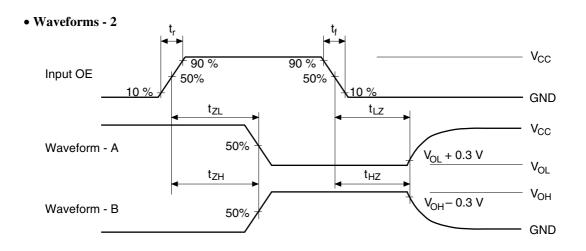
• $C_r = 50 \text{ pF}$

Item	Symbol	V _{cc} (V)	Ta = 2	Ta = 25°C			Test Conditions
			Min	Тур	Max		
Power dissipation	C _{PD}	3.3	_	10.5	_	pF	f = 10 MHz
capacitance		5.0	_	11.5	_		

Test Circuit



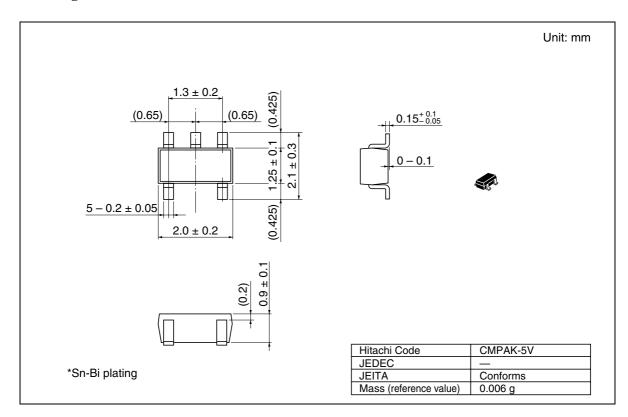


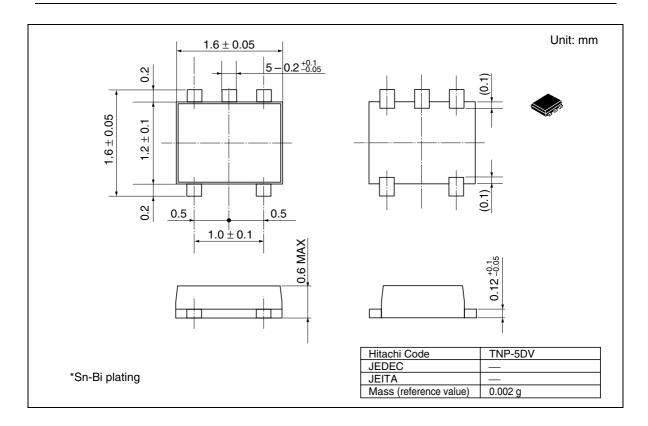


Notes: 1. Input waveform : PRR \leq 1 MHz, Zo = 50 Ω , $t_r \leq$ 3 ns, $t_f \leq$ 3 ns.

- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions





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Sales Offices

ITACH

Hitachi. Ltd.

Semiconductor & Integrated Circuits Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: (03) 3270-2111 Fax: (03) 3270-5109

http://www.hitachisemiconductor.com/

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive San Jose CA 95134 Tel: <1> (408) 433-1990 Maidenhead

Hitachi Europe Ltd. Electronic Components Group Whitebrook Park Lower Cookham Boad

Fax: <1>(408) 433-0223 Berkshire SL6 8YA, United Kingdom Fax: <65>-6538-6933/6538-3877 Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

> Hitachi Europe GmbH Electronic Components Group Dornacher Str 3 D-85622 Feldkirchen Postfach 201, D-85619 Feldkirchen Germany

Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Asia Ltd Hitachi Tower 16 Collyer Quay #20-00 Singapore 049318 Tel: <65>-6538-6533/6538-8577

URL: http://semiconductor.hitachi.com.sg

Hitachi Asia Ltd. (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road Hung-Kuo Building Taipei (105), Taiwan Tel: <886>-(2)-2718-3666 Fax: <886>-(2)-2718-8180 Telex: 23222 HAS-TP

URL: http://semiconductor.hitachi.com.tw

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Hitachi Asia (Hong Kong) Ltd.

Harbour City, Canton Road

7/F., North Tower

World Finance Centre

Tel: <852>-2735-9218 Fax: <852>-2730-0281

Group III (Electronic Components)

Tsim Sha Tsui, Kowloon Hong Kong

URL: http://semiconductor.hitachi.com.hk

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